



BC856S Dual Transistor(PNP+PNP)

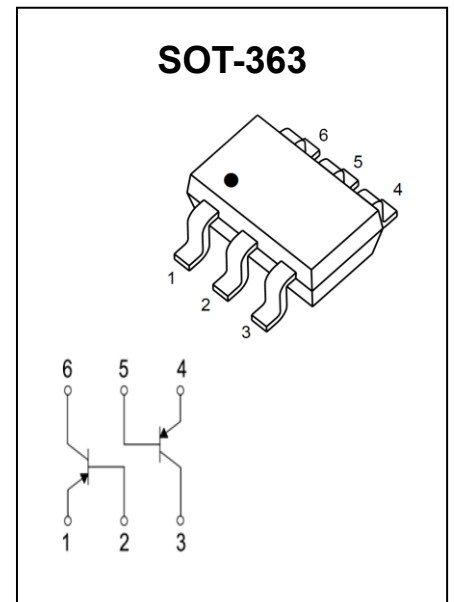
Application

- This device is designed for general purpose amplifier applications

Marking: 5Ft

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

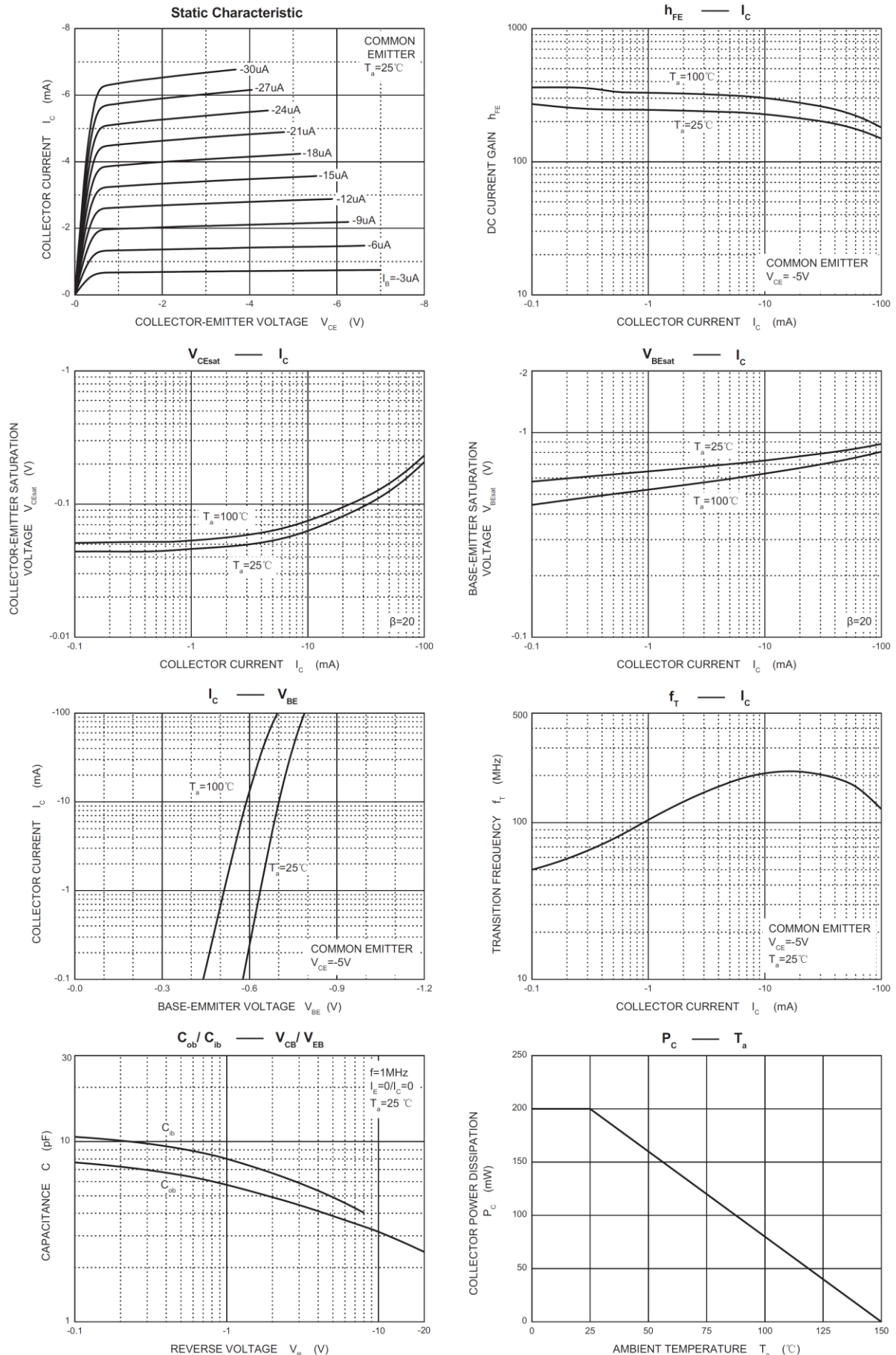
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-65	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current -Continuous	I _C	-0.1	A
Collector Power Dissipation	P _C	0.2	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

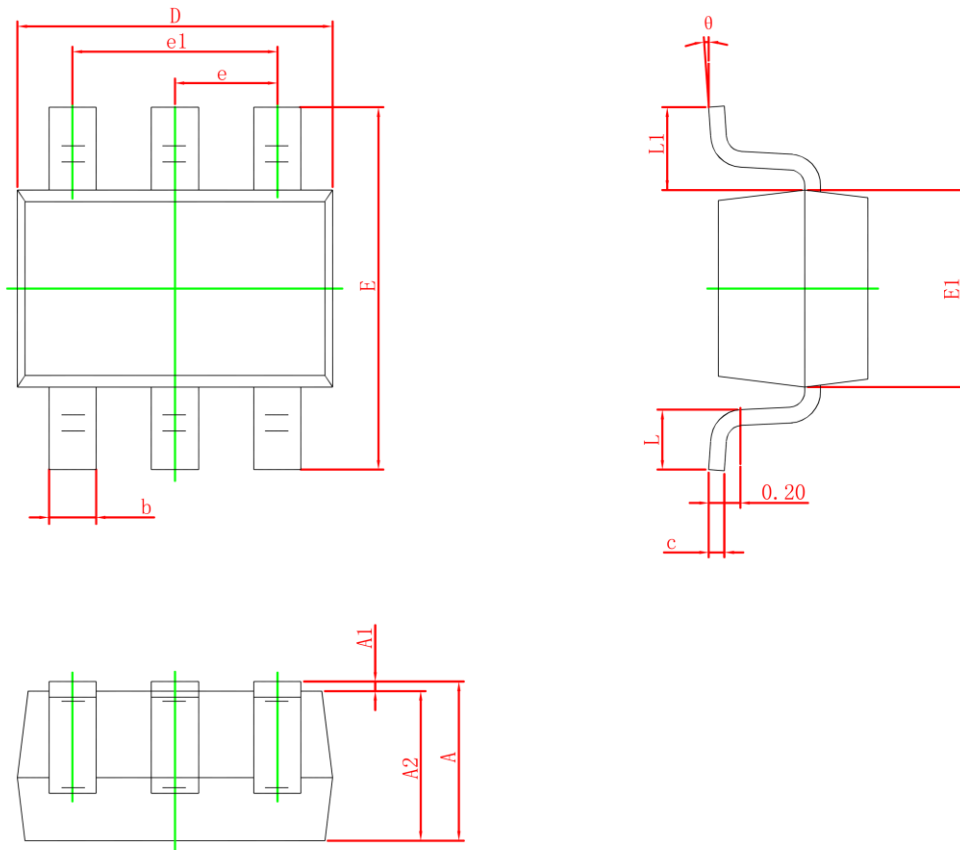


ELECTRICAL CHARACTERISTICS(T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-65			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V, I _E =0V			-15	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0V			-100	nA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-2mA	110			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10mA, I _B = -0.5mA			-0.1	V
		I _C =-100mA, I _B = -5mA			-0.3	V
Base-emitter voltage	V _{BE(on)}	I _C =-10mA, I _B = -0.5mA		-0.7		V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			2.5	pF
Transition frequency	f _T	V _{CE} = -5V, I _C =-10mA, f=100MHz	100			MHZ

Typical Characteristics



SOT-363 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A1	0	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.080	0.150	0.003	0.006
D	1.800	2.200	0.071	0.087
E	2.000	2.450	0.079	0.096
E1	1.150	1.350	0.045	0.053
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L1	0.525REF		0.021REF	
L	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°